What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Brown-out Detect/Reset, CapSense, LCD, LVD, POR, PWM, WDT
Number of I/O	36
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 16x10b Slope; D/A 2xIDAC
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-TQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4124azi-s413t

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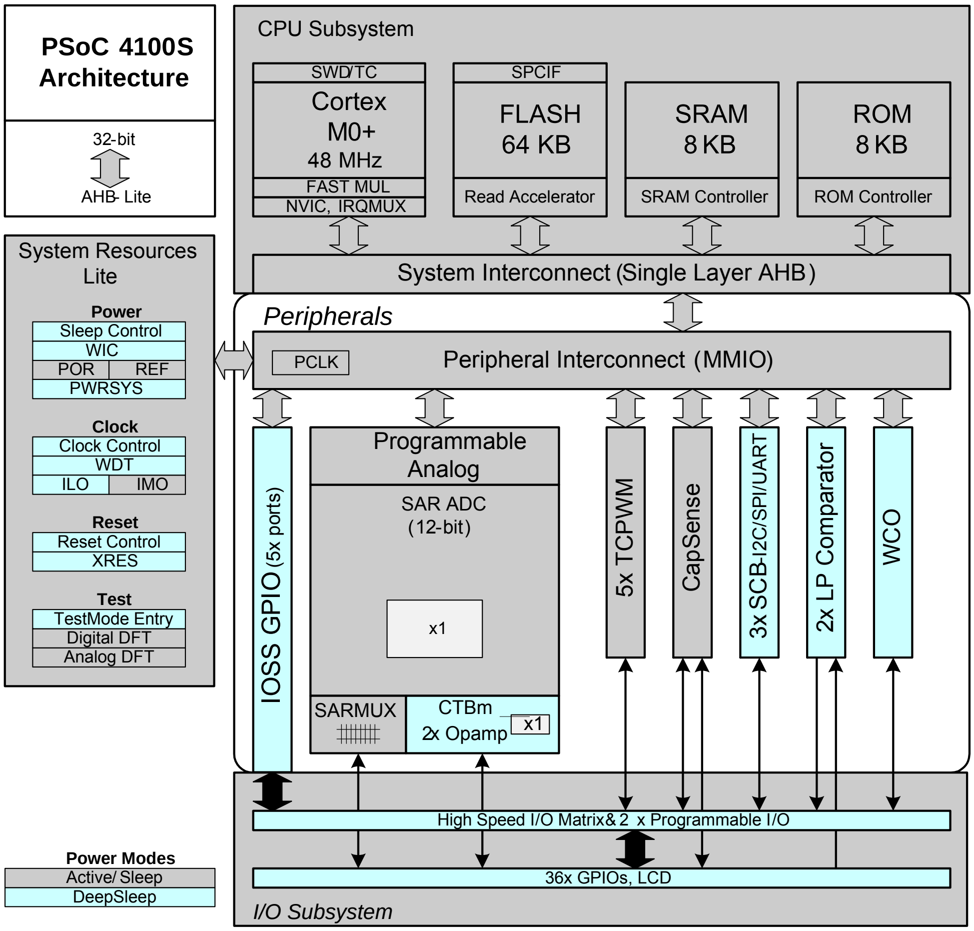


Figure 1. Block Diagram

PSoC 4100S devices include extensive support for programming, testing, debugging, and tracing both hardware and firmware.

The ARM Serial-Wire Debug (SWD) interface supports all programming and debug features of the device.

Complete debug-on-chip functionality enables full-device debugging in the final system using the standard production device. It does not require special interfaces, debugging pods, simulators, or emulators. Only the standard programming connections are required to fully support debug.

The PSoC Creator IDE provides fully integrated programming and debug support for the PSoC 4100S devices. The SWD interface is fully compatible with industry-standard third-party tools. The PSoC 4100S family provides a level of security not possible with multi-chip application solutions or with microcontrollers. It has the following advantages:

- Allows disabling of debug features
- Robust flash protection
- Allows customer-proprietary functionality to be implemented in on-chip programmable blocks

The debug circuits are enabled by default and can be disabled in firmware. If they are not enabled, the only way to re-enable them is to erase the entire device, clear flash protection, and reprogram the device with new firmware that enables debugging. Thus firmware control of debugging cannot be over-ridden without erasing the firmware thus providing security.

Additionally, all device interfaces can be permanently disabled (device security) for applications concerned about phishing attacks due to a maliciously reprogrammed device or attempts to defeat security by starting and interrupting flash programming sequences. All programming, debug, and test interfaces are disabled when maximum device security is enabled. Therefore, PSoC 4100S, with device security enabled, may not be returned for failure analysis. This is a trade-off the PSoC 4100S allows the customer to make.

Reset

The PSoC 4100S can be reset from a variety of sources including a software reset. Reset events are asynchronous and guarantee reversion to a known state. The reset cause is recorded in a register, which is sticky through reset and allows software to determine the cause of the reset. An XRES pin is reserved for external reset by asserting it active low. The XRES pin has an internal pull-up resistor that is always enabled.

Analog Blocks

12-bit SAR ADC

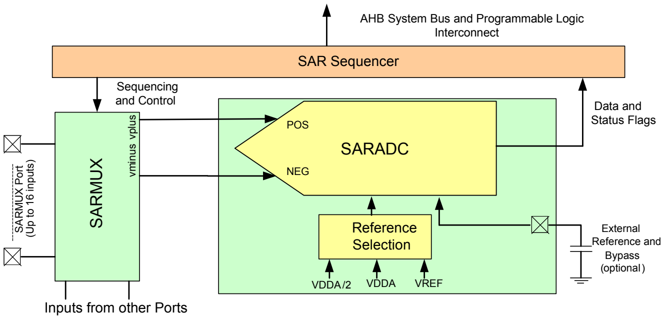
The 12-bit, 1-Msps SAR ADC can operate at a maximum clock rate of 18 MHz and requires a minimum of 18 clocks at that frequency to do a 12-bit conversion.

The Sample-and-Hold (S/H) aperture is programmable allowing the gain bandwidth requirements of the amplifier driving the SAR inputs, which determine its settling time, to be relaxed if required. It is possible to provide an external bypass (through a fixed pin location) for the internal reference amplifier.

The SAR is connected to a fixed set of pins through an 8-input sequencer. The sequencer cycles through selected channels autonomously (sequencer scan) with zero switching overhead (that is, aggregate sampling bandwidth is equal to 1 Msps whether it is for a single channel or distributed over several channels). The sequencer switching is effected through a state machine or through firmware driven switching. A feature provided by the sequencer is buffering of each channel to reduce CPU interrupt service requirements. To accommodate signals with varying source impedance and frequency, it is possible to have different sample times programmable for each channel. Also, signal range specification through a pair of range registers (low and high range values) is implemented with a corresponding out-of-range interrupt if the digitized value exceeds the programmed range; this allows fast detection of out-of-range values without the necessity of having to wait for a sequencer scan to be completed and the CPU to read the values and check for out-of-range values in software.

The SAR is not available in Deep Sleep mode as it requires a high-speed clock (up to 18 MHz). The SAR operating range is 1.71 V to 5.5 V.

Figure 3. SAR ADC



Two Opamps (Continuous-Time Block; CTB)

The PSoC 4100S has two opamps with Comparator modes which allow most common analog functions to be performed on-chip eliminating external components; PGAs, Voltage Buffers, Filters, Trans-Impedance Amplifiers, and other functions can be realized, in some cases with external passives. saving power, cost, and space. The on-chip opamps are designed with enough bandwidth to drive the Sample-and-Hold circuit of the ADC without requiring external buffering.

Low-power Comparators (LPC)

The PSoC 4100S has a pair of low-power comparators, which can also operate in Deep Sleep modes. This allows the analog system blocks to be disabled while retaining the ability to monitor external voltage levels during low-power modes. The comparator outputs are normally synchronized to avoid metastability unless operating in an asynchronous power mode where the system wake-up circuit is activated by a comparator switch event. The LPC outputs can be routed to pins.

Current DACs

The PSoC 4100S has two IDACs, which can drive any of the pins on the chip. These IDACs have programmable current ranges.

Analog Multiplexed Buses

The PSoC 4100S has two concentric independent buses that go around the periphery of the chip. These buses (called amux buses) are connected to firmware-programmable analog switches that allow the chip's internal resources (IDACs, comparator) to connect to any pin on the I/O Ports.

Programmable Digital Blocks

The Programmable I/O (Smart I/O) block is a fabric of switches and LUTs that allows Boolean functions to be performed in signals being routed to the pins of a GPIO port. The Smart I/O can perform logical operations on input pins to the chip and on signals going out as outputs.

Fixed Function Digital

Timer/Counter/PWM (TCPWM) Block

The TCPWM block consists of a 16-bit counter with user-programmable period length. There is a capture register to record the count value at the time of an event (which may be an I/O event), a period register that is used to either stop or auto-reload the counter when its count is equal to the period register, and compare registers to generate compare value signals that are used as PWM duty cycle outputs. The block also provides true and complementary outputs with programmable offset between them to allow use as dead-band programmable complementary PWM outputs. It also has a Kill input to force outputs to a predetermined state; for example, this is used in motor drive systems when an over-current state is indicated and the PWM driving the FETs needs to be shut off immediately with no time for software intervention. There are five TCPWM blocks in the PSoC 4100S.

Serial Communication Block (SCB)

The PSoC 4100S has three serial communication blocks, which can be programmed to have SPI, I2C, or UART functionality.

I^2C Mode: The hardware I^2C block implements a full multi-master and slave interface (it is capable of multi-master arbitration). This block is capable of operating at speeds of up to 400 kbps (Fast Mode) and has flexible buffering options to reduce interrupt overhead and latency for the CPU. It also

Table 1. Pin List *(continued)*

48-TQFP		44-TQFP		40-QFN		32-QFN		35-CSP	
Pin	**Name**	**Pin**	**Name**	**Pin**	**Name**	**Pin**	**Name**	**Pin**	**Name**
19	P3.6	17	P3.6	16	P3.6				
20	P3.7	18	P3.7	17	P3.7				
21	VDDD	19	VDDD						
22	P4.0	20	P4.0	18	P4.0	13	P4.0	B1	P4.0
23	P4.1	21	P4.1	19	P4.1	14	P4.1	B2	P4.1
24	P4.2	22	P4.2	20	P4.2	15	P4.2	A2	P4.2
25	P4.3	23	P4.3	21	P4.3	16	P4.3	A1	P4.3

Notes: Pins 11, 15, 26, and 27 are No Connects (NC) on the 48-pin TQFP.

Descriptions of the Power pins are as follows:

VDDD: Power supply for the digital section.

VDDA: Power supply for the analog section.

VSSD, VSSA: Ground pins for the digital and analog sections respectively.

VCCD: Regulated digital supply (1.8 V ±5%)

VDD: Power supply to all sections of the chip

VSS: Ground for all sections of the chip

Development Support

The PSoC 4100S family has a rich set of documentation, development tools, and online resources to assist you during your development process. Visit www.cypress.com/go/psoc4 to find out more.

Documentation

A suite of documentation supports the PSoC 4100S family to ensure that you can find answers to your questions quickly. This section contains a list of some of the key documents.

Software User Guide: A step-by-step guide for using PSoC Creator. The software user guide shows you how the PSoC Creator build process works in detail, how to use source control with PSoC Creator, and much more.

Component Datasheets: The flexibility of PSoC allows the creation of new peripherals (components) long after the device has gone into production. Component data sheets provide all of the information needed to select and use a particular component, including a functional description, API documentation, example code, and AC/DC specifications.

Application Notes: PSoC application notes discuss a particular application of PSoC in depth; examples include brushless DC motor control and on-chip filtering. Application notes often include example projects in addition to the application note document.

Technical Reference Manual: The Technical Reference Manual (TRM) contains all the technical detail you need to use a PSoC device, including a complete description of all PSoC registers. The TRM is available in the Documentation section at www.cypress.com/psoc4.

Online

In addition to print documentation, the Cypress PSoC forums connect you with fellow PSoC users and experts in PSoC from around the world, 24 hours a day, 7 days a week.

Tools

With industry standard cores, programming, and debugging interfaces, the PSoC 4100S family is part of a development tool ecosystem. Visit us at www.cypress.com/go/psoccreator for the latest information on the revolutionary, easy to use PSoC Creator IDE, supported third party compilers, programmers, debuggers, and development kits.

Table 3. DC Specifications *(continued)*

Typical values measured at V_{DD} = 3.3 V and 25 °C.

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
Sleep Mode, VDDD = 1.8 V to 5.5 V (Regulator on)							
SID22	IDD17	I^2C wakeup WDT, and Comparators on	–	1.7	2.2	mA	6 MHZ. Max is at 85 °C and 5.5 V.
SID25	IDD20	I^2C wakeup, WDT, and Comparators on.	–	2.2	2.5		12 MHZ. Max is at 85 °C and 5.5 V.
Sleep Mode, V_{DDD} = 1.71 V to 1.89 V (Regulator bypassed)							
SID28	IDD23	I^2C wakeup, WDT, and Comparators on	–	0.7	0.9	mA	6 MHZ. Max is at 85 °C and 5.5 V.
SID28A	IDD23A	I^2C wakeup, WDT, and Comparators on	–	1	1.2	mA	12 MHZ. Max is at 85 °C and 5.5 V.
Deep Sleep Mode, V_{DD} = 1.8 V to 3.6 V (Regulator on)							
SID31	I_{DD26}	I^2C wakeup and WDT on	–	2.5	60	µA	Max is at 3.6 V and 85 °C.
Deep Sleep Mode, V_{DD} = 3.6 V to 5.5 V (Regulator on)							
SID34	I_{DD29}	I^2C wakeup and WDT on	–	2.5	60	µA	Max is at 5.5 V and 85 °C.
Deep Sleep Mode, V_{DD} = V_{CCD} = 1.71 V to 1.89 V (Regulator bypassed)							
SID37	I_{DD32}	I^2C wakeup and WDT on	–	2.5	65	µA	Max is at 1.89 V and 85 °C.
XRES Current							
SID307	I_{DD_XR}	Supply current while XRES asserted	–	2	5	mA	–

Table 4. AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID48	F_{CPU}	CPU frequency	DC	–	48	MHz	$1.71 \le V_{DD} \le 5.5$
SID49[3]	T_{SLEEP}	Wakeup from Sleep mode	–	0	–	µs	
SID50[3]	$T_{DEEPSLEEP}$	Wakeup from Deep Sleep mode	–	35	–		

Note

2. Guaranteed by characterization.

GPIO

Table 5. GPIO DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID57	V_{IH}[3]	Input voltage high threshold	0.7 × V_{DDD}	–	–	V	CMOS Input
SID58	V_{IL}	Input voltage low threshold	–	–	0.3 × V_{DDD}		CMOS Input
SID241	V_{IH}[3]	LVTTL input, $V_{DDD} < 2.7$ V	0.7 × V_{DDD}	–	–		–
SID242	V_{IL}	LVTTL input, $V_{DDD} < 2.7$ V	–	–	0.3 × V_{DDD}		–
SID243	V_{IH}[3]	LVTTL input, $V_{DDD} \geq 2.7$ V	2.0	–	–		–
SID244	V_{IL}	LVTTL input, $V_{DDD} \geq 2.7$ V	–	–	0.8		–
SID59	V_{OH}	Output voltage high level	V_{DDD} –0.6	–	–		I_{OH} = 4 mA at 3 V V_{DDD}
SID60	V_{OH}	Output voltage high level	V_{DDD} –0.5	–	–		I_{OH} = 1 mA at 1.8 V V_{DDD}
SID61	V_{OL}	Output voltage low level	–	–	0.6		I_{OL} = 4 mA at 1.8 V V_{DDD}
SID62	V_{OL}	Output voltage low level	–	–	0.6		I_{OL} = 10 mA at 3 V V_{DDD}
SID62A	V_{OL}	Output voltage low level	–	–	0.4		I_{OL} = 3 mA at 3 V V_{DDD}
SID63	R_{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	–
SID64	$R_{PULLDOWN}$	Pull-down resistor	3.5	5.6	8.5		–
SID65	I_{IL}	Input leakage current (absolute value)	–	–	2	nA	25 °C, V_{DDD} = 3.0 V
SID66	C_{IN}	Input capacitance	–	–	7	pF	–
SID67[4]	V_{HYSTTL}	Input hysteresis LVTTL	25	40	–	mV	$V_{DDD} \geq 2.7$ V
SID68[4]	$V_{HYSCMOS}$	Input hysteresis CMOS	0.05 × V_{DDD}	–	–		$V_{DD} < 4.5$ V
SID68A[4]	$V_{HYSCMOS5V5}$	Input hysteresis CMOS	200	–	–		$V_{DD} > 4.5$ V
SID69[4]	I_{DIODE}	Current through protection diode to V_{DD}/V_{SS}	–	–	100	µA	–
SID69A[4]	I_{TOT_GPIO}	Maximum total source or sink chip current	–	–	200	mA	–

Table 6. GPIO AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID70	T_{RISEF}	Rise time in fast strong mode	2	–	12	ns	3.3 V V_{DDD}, Cload = 25 pF
SID71	T_{FALLF}	Fall time in fast strong mode	2	–	12		3.3 V V_{DDD}, Cload = 25 pF
SID72	T_{RISES}	Rise time in slow strong mode	10	–	60	–	3.3 V V_{DDD}, Cload = 25 pF

Notes

[3] V_{IH} must not exceed V_{DDD} + 0.2 V.

[4] Guaranteed by characterization.

Table 6. GPIO AC Specifications

(Guaranteed by Characterization) *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID73	T_{FALLS}	Fall time in slow strong mode	10	–	60	–	3.3 V V_{DDD}, Cload = 25 pF
SID74	$F_{GPIOUT1}$	GPIO F_{OUT}; 3.3 V ≤ V_{DDD} ≤ 5.5 V Fast strong mode	–	–	33	MHz	90/10%, 25 pF load, 60/40 duty cycle
SID75	$F_{GPIOUT2}$	GPIO F_{OUT}; 1.71 V≤ V_{DDD}≤ 3.3 V Fast strong mode	–	–	16.7		90/10%, 25 pF load, 60/40 duty cycle
SID76	$F_{GPIOUT3}$	GPIO F_{OUT}; 3.3 V ≤ V_{DDD} ≤ 5.5 V Slow strong mode	–	–	7		90/10%, 25 pF load, 60/40 duty cycle
SID245	$F_{GPIOUT4}$	GPIO F_{OUT}; 1.71 V ≤ V_{DDD} ≤ 3.3 V Slow strong mode.	–	–	3.5		90/10%, 25 pF load, 60/40 duty cycle
SID246	F_{GPIOIN}	GPIO input operating frequency; 1.71 V ≤ V_{DDD} ≤ 5.5 V	–	–	48		90/10% V_{IO}

XRES

Table 7. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID77	V_{IH}	Input voltage high threshold	0.7 × V_{DDD}	–	–	V	CMOS Input
SID78	V_{IL}	Input voltage low threshold	–	–	0.3 × V_{DDD}		
SID79	R_{PULLUP}	Pull-up resistor	–	60	–	kΩ	–
SID80	C_{IN}	Input capacitance	–	–	7	pF	–
SID81[5]	$V_{HYSXRES}$	Input voltage hysteresis	–	100	–	mV	Typical hysteresis is 200 mV for V_{DD} > 4.5 V
SID82	I_{DIODE}	Current through protection diode to V_{DD}/V_{SS}	–	–	100	μA	

Table 8. XRES AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID83[5]	$T_{RESETWIDTH}$	Reset pulse width	1	–	–	μs	–
BID194[5]	$T_{RESETWAKE}$	Wake-up time from reset release	–	–	2.7	ms	–

Note

5. Guaranteed by characterization.

Table 9. CTBm Opamp Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
		General opamp specs for both internal and external modes					
SID281	V_{IN}	Charge-pump on, V_{DDA} = 2.7 V	–0.05	–	V_{DDA}-0.2	V	–
SID282	V_{CM}	Charge-pump on, V_{DDA} = 2.7 V	–0.05	–	V_{DDA}-0.2		–
	V_{OUT}	V_{DDA} = 2.7 V					
SID283	V_{OUT_1}	power=hi, Iload=10 mA	0.5	–	V_{DDA} -0.5	V	–
SID284	V_{OUT_2}	power=hi, Iload=1 mA	0.2	–	V_{DDA} -0.2		–
SID285	V_{OUT_3}	power=med, Iload=1 mA	0.2	–	V_{DDA} -0.2		–
SID286	V_{OUT_4}	power=lo, Iload=0.1 mA	0.2	–	V_{DDA} -0.2		–
SID288	V_{OS_TR}	Offset voltage, trimmed	–1.0	±0.5	1.0	mV	High mode, input 0 V to V_{DDA}-0.2 V
SID288A	V_{OS_TR}	Offset voltage, trimmed	–	±1	–		Medium mode, input 0 V to V_{DDA}-0.2 V
SID288B	V_{OS_TR}	Offset voltage, trimmed	–	±2	–		Low mode, input 0 V to V_{DDA}-0.2 V
SID290	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–10	±3	10	µV/C	High mode
SID290A	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–	µV/C	Medium mode
SID290B	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–		Low mode
SID291	CMRR	DC	70	80	–	dB	Input is 0 V to V_{DDA}-0.2 V, Output is 0.2 V to V_{DDA}-0.2 V
SID292	PSRR	At 1 kHz, 10-mV ripple	70	85	–		V_{DDD} = 3.6 V, high-power mode, input is 0.2 V to V_{DDA}-0.2 V
	Noise						
SID294	VN2	Input-referred, 1 kHz, power=Hi	–	72	–	nV/rtHz	3
SID295	VN3	Input-referred, 10 kHz, power=Hi	–	28	–		Input and output are at 0.2 V to V_{DDA}-0.2 V
SID296	VN4	Input-referred, 100 kHz, power=Hi	–	15	–		Input and output are at 0.2 V to V_{DDA}-0.2 V
SID297	C_{LOAD}	Stable up to max. load. Performance specs at 50 pF.	–	–	125	pF	–
SID298	SLEW_RATE	Cload = 50 pF, Power = High, V_{DDA} = 2.7 V	6	–	–	V/µs	–

CSD

Table 14. CSD and IDAC Specifications

SPEC ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SYS.PER#3	VDD_RIPPLE	Max allowed ripple on power supply, DC to 10 MHz	–	–	±50	mV	V_{DD} > 2 V (with ripple), 25 °C T_A, Sensitivity = 0.1 pF
SYS.PER#16	VDD_RIPPLE_1.8	Max allowed ripple on power supply, DC to 10 MHz	–	–	±25	mV	V_{DD} > 1.75V (with ripple), 25 °C T_A, Parasitic Capacitance (C_P) < 20 pF, Sensitivity ≥ 0.4 pF
SID.CSD.BLK	ICSD	Maximum block current	–	–	4000	µA	Maximum block current for both IDACs in dynamic (switching) mode including comparators, buffer, and reference generator.
SID.CSD#15	V_{REF}	Voltage reference for CSD and Comparator	0.6	1.2	V_{DDA} - 0.6	V	V_{DDA} - 0.06 or 4.4, whichever is lower
SID.CSD#15A	VREF_EXT	External Voltage reference for CSD and Comparator	0.6		V_{DDA} - 0.6	V	V_{DDA} - 0.06 or 4.4, whichever is lower
SID.CSD#16	IDAC1IDD	IDAC1 (7-bits) block current	–	–	1750	µA	
SID.CSD#17	IDAC2IDD	IDAC2 (7-bits) block current	–	–	1750	µA	
SID308	VCSD	Voltage range of operation	1.71	–	5.5	V	1.8 V ±5% or 1.8 V to 5.5 V
SID308A	VCOMPIDAC	Voltage compliance range of IDAC	0.6	–	V_{DDA} –0.6	V	V_{DDA} - 0.06 or 4.4, whichever is lower
SID309	IDAC1DNL	DNL	–1	–	1	LSB	
SID310	IDAC1INL	INL	–2	–	2	LSB	INL is ±5.5 LSB for V_{DDA} < 2 V
SID311	IDAC2DNL	DNL	–1	–	1	LSB	
SID312	IDAC2INL	INL	–2	–	2	LSB	INL is ±5.5 LSB for V_{DDA} < 2 V
SID313	SNR	Ratio of counts of finger to noise. Guaranteed by characterization	5	–	–	Ratio	Capacitance range of 5 to 35 pF, 0.1-pF sensitivity. All use cases. V_{DDA} > 2 V.
SID314	IDAC1CRT1	Output current of IDAC1 (7 bits) in low range	4.2	–	5.4	µA	LSB = 37.5-nA typ.
SID314A	IDAC1CRT2	Output current of IDAC1(7 bits) in medium range	34	–	41	µA	LSB = 300-nA typ.
SID314B	IDAC1CRT3	Output current of IDAC1(7 bits) in high range	275	–	330	µA	LSB = 2.4-µA typ.
SID314C	IDAC1CRT12	Output current of IDAC1 (7 bits) in low range, 2X mode	8	–	10.5	µA	LSB = 75-nA typ.
SID314D	IDAC1CRT22	Output current of IDAC1(7 bits) in medium range, 2X mode	69	–	82	µA	LSB = 600-nA typ.
SID314E	IDAC1CRT32	Output current of IDAC1(7 bits) in high range, 2X mode	540	–	660	µA	LSB = 4.8-µA typ.
SID315	IDAC2CRT1	Output current of IDAC2 (7 bits) in low range	4.2	–	5.4	µA	LSB = 37.5-nA typ.
SID315A	IDAC2CRT2	Output current of IDAC2 (7 bits) in medium range	34	–	41	µA	LSB = 300-nA typ.
SID315B	IDAC2CRT3	Output current of IDAC2 (7 bits) in high range	275	–	330	µA	LSB = 2.4-µA typ.
SID315C	IDAC2CRT12	Output current of IDAC2 (7 bits) in low range, 2X mode	8	–	10.5	µA	LSB = 75-nA typ.
SID315D	IDAC2CRT22	Output current of IDAC2(7 bits) in medium range, 2X mode	69	–	82	µA	LSB = 600-nA typ.
SID315E	IDAC2CRT32	Output current of IDAC2(7 bits) in high range, 2X mode	540	–	660	µA	LSB = 4.8-µA typ.
SID315F	IDAC3CRT13	Output current of IDAC in 8-bit mode in low range	8	–	10.5	µA	LSB = 37.5-nA typ.

Table 19. SPI DC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID163	ISPI1	Block current consumption at 1 Mbps	–	–	360	µA	–
SID164	ISPI2	Block current consumption at 4 Mbps	–	–	560		–
SID165	ISPI3	Block current consumption at 8 Mbps	–	–	600		–

Table 20. SPI AC Specifications[8]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID166	FSPI	SPI Operating frequency (Master; 6X Oversampling)	–	–	8	MHz	SID166
Fixed SPI Master Mode AC Specifications							
SID167	TDMO	MOSI Valid after SClock driving edge	–	–	15	ns	–
SID168	TDSI	MISO Valid before SClock capturing edge	20	–	–		Full clock, late MISO sampling
SID169	THMO	Previous MOSI data hold time	0	–	–		Referred to Slave capturing edge
Fixed SPI Slave Mode AC Specifications							
SID170	TDMI	MOSI Valid before Sclock Capturing edge	40	–	–	ns	–
SID171	TDSO	MISO Valid after Sclock driving edge	–	–	42 + 3*Tcpu		$T_{CPU} = 1/F_{CPU}$
SID171A	TDSO_EXT	MISO Valid after Sclock driving edge in Ext. Clk mode	–	–	48		–
SID172	THSO	Previous MISO data hold time	0	–	–		–
SID172A	TSSELSSCK	SSEL Valid to first SCK Valid edge	–	–	100	ns	–

Table 21. UART DC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID160	I_{UART1}	Block current consumption at 100 Kbps	–	–	55	µA	–
SID161	I_{UART2}	Block current consumption at 1000 Kbps	–	–	312	µA	–

Table 22. UART AC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID162	F_{UART}	Bit rate	–	–	1	Mbps	–

Table 23. LCD Direct Drive DC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID154	I_{LCDLOW}	Operating current in low power mode	–	5	–	µA	16 × 4 small segment disp. at 50 Hz
SID155	C_{LCDCAP}	LCD capacitance per segment/common driver	–	500	5000	pF	–
SID156	LCD_{OFFSET}	Long-term segment offset	–	20	–	mV	–
SID157	I_{LCDOP1}	LCD system operating current Vbias = 5 V	–	2	–	mA	32 × 4 segments. 50 Hz. 25 °C
SID158	I_{LCDOP2}	LCD system operating current Vbias = 3.3 V	–	2	–		32 × 4 segments. 50 Hz. 25 °C

Table 24. LCD Direct Drive AC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID159	F_{LCD}	LCD frame rate	10	50	150	Hz	–

Note

[9] Guaranteed by characterization.

Memory

Table 25. Flash DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID173	V_{PE}	Erase and program voltage	1.71	–	5.5	V	–

Table 26. Flash AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID174	$T_{ROWWRITE}$[10]	Row (block) write time (erase and program)	–	–	20	ms	Row (block) = 128 bytes
SID175	$T_{ROWERASE}$[10]	Row erase time	–	–	16		–
SID176	$T_{ROWPROGRAM}$[10]	Row program time after erase	–	–	4		–
SID178	$T_{BULKERASE}$[10]	Bulk erase time (64 KB)	–	–	35		–
SID180[11]	$T_{DEVPROG}$[10]	Total device program time	–	–	7	Seconds	–
SID181[11]	F_{END}	Flash endurance	100 K	–	–	Cycles	–
SID182[11]	F_{RET}	Flash retention. $T_A \leq$ 55 °C, 100 K P/E cycles	20	–	–	Years	–
SID182A[11]	–	Flash retention. $T_A \leq$ 85 °C, 10 K P/E cycles	10	–	–		–
SID256	TWS48	Number of Wait states at 48 MHz	2	–	–		CPU execution from Flash
SID257	TWS24	Number of Wait states at 24 MHz	1	–	–		CPU execution from Flash

System Resources

Power-on Reset (POR)

Table 27. Power On Reset (PRES)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.CLK#6	SR_POWER_UP	Power supply slew rate	1	–	67	V/ms	At power-up
SID185[11]	$V_{RISEIPOR}$	Rising trip voltage	0.80	–	1.5	V	–
SID186[11]	$V_{FALLIPOR}$	Falling trip voltage	0.70	–	1.4		–

Table 28. Brown-out Detect (BOD) for V_{CCD}

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID190[11]	$V_{FALLPPOR}$	BOD trip voltage in active and sleep modes	1.48	–	1.62	V	–
SID192[11]	$V_{FALLDPSLP}$	BOD trip voltage in Deep Sleep	1.11	–	1.5		–

Notes

[10] It can take as much as 20 milliseconds to write to Flash. During this time the device should not be Reset, or Flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin, software resets, CPU lockup states and privilege violations, improper power supply levels, and watchdogs. Make certain that these are not inadvertently activated.

[11] Guaranteed by characterization.

SWD Interface

Table 29. SWD Interface Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID213	F_SWDCLK1	3.3 V ≤ V_{DD} ≤ 5.5 V	–	–	14	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID214	F_SWDCLK2	1.71 V ≤ V_{DD} ≤ 3.3 V	–	–	7		SWDCLK ≤ 1/3 CPU clock frequency
SID215[12]	T_SWDI_SETUP	T = 1/f SWDCLK	0.25*T	–	–	ns	–
SID216[12]	T_SWDI_HOLD	T = 1/f SWDCLK	0.25*T	–	–		–
SID217[12]	T_SWDO_VALID	T = 1/f SWDCLK	–	–	0.5*T		–
SID217A[12]	T_SWDO_HOLD	T = 1/f SWDCLK	1	–	–		–

Internal Main Oscillator

Table 30. IMO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID218	I_{IMO1}	IMO operating current at 48 MHz	–	–	250	µA	–
SID219	I_{IMO2}	IMO operating current at 24 MHz	–	–	180	µA	–

Table 31. IMO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID223	$F_{IMOTOL1}$	Frequency variation at 24, 32, and 48 MHz (trimmed)	–	–	±2	%	
SID226	$T_{STARTIMO}$	IMO startup time	–	–	7	µs	–
SID228	$T_{JITRMSIMO2}$	RMS jitter at 24 MHz	–	145	–	ps	–

Internal Low-Speed Oscillator

Table 32. ILO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID231[12]	I_{ILO1}	ILO operating current	–	0.3	1.05	µA	–

Table 33. ILO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID234[12]	$T_{STARTILO1}$	ILO startup time	–	–	2	ms	–
SID236[12]	$T_{ILODUTY}$	ILO duty cycle	40	50	60	%	–
SID237	$F_{ILOTRIM1}$	ILO frequency range	20	40	80	kHz	–

Note

[12] Guaranteed by characterization.

Table 34. Watch Crystal Oscillator (WCO) Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID398	FWCO	Crystal Frequency	–	32.768	–	kHz	
SID399	FTOL	Frequency tolerance	–	50	250	ppm	With 20-ppm crystal
SID400	ESR	Equivalent series resistance	–	50	–	kΩ	
SID401	PD	Drive Level	–	–	1	µW	
SID402	TSTART	Startup time	–	–	500	ms	
SID403	CL	Crystal Load Capacitance	6	–	12.5	pF	
SID404	C0	Crystal Shunt Capacitance	–	1.35	–	pF	
SID405	IWCO1	Operating Current (high power mode)	–	–	8	uA	
SID406	IWCO2	Operating Current (low power mode)	–	–	1	uA	

Table 35. External Clock Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID305[13]	ExtClkFreq	External clock input frequency	0	–	48	MHz	–
SID306[13]	ExtClkDuty	Duty cycle; measured at $V_{DD/2}$	45	–	55	%	–

Table 36. Block Specs

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID262[13]	$T_{CLKSWITCH}$	System clock source switching time	3	–	4	Periods	–

Table 37. Smart I/O Pass-through Time (Delay in Bypass Mode)

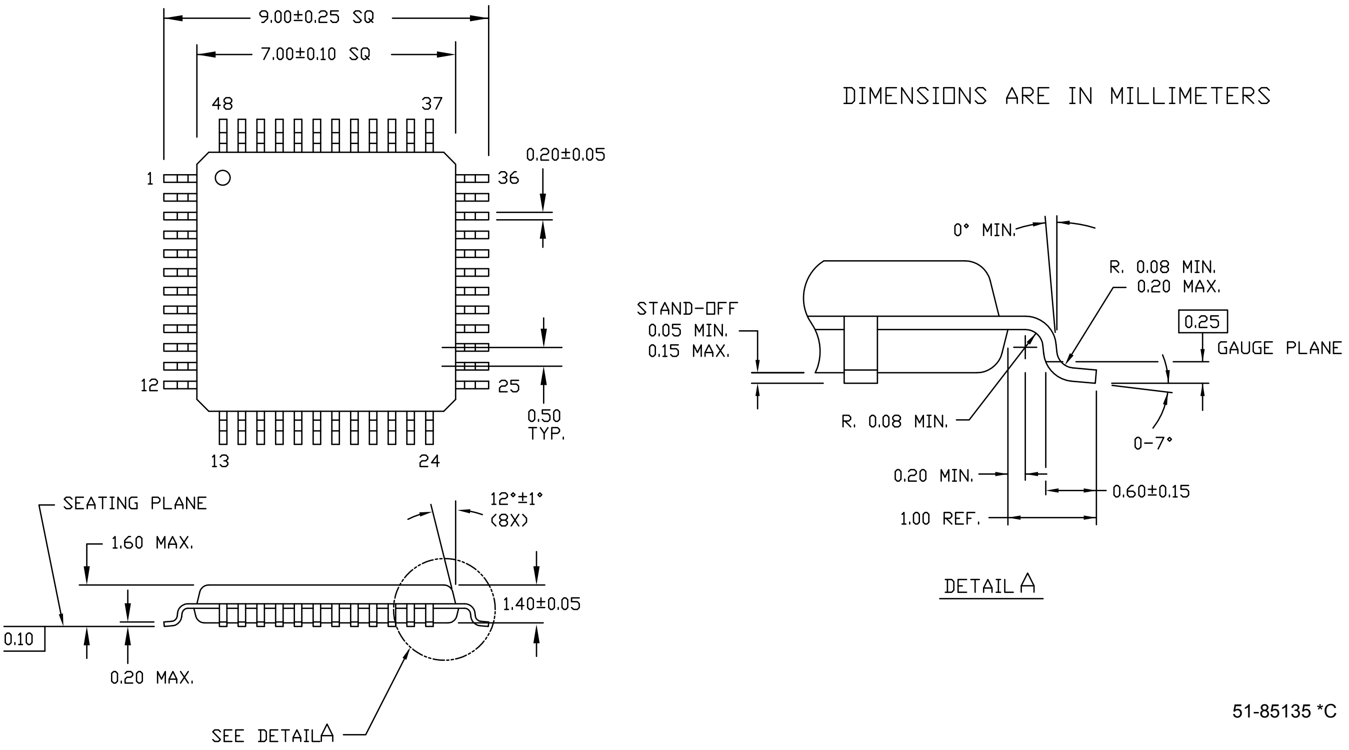
Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID252	PRG_BYPASS	Max delay added by Smart I/O in bypass mode	–	–	1.6	ns	

Note

[13] Guaranteed by characterization.

Package Diagrams

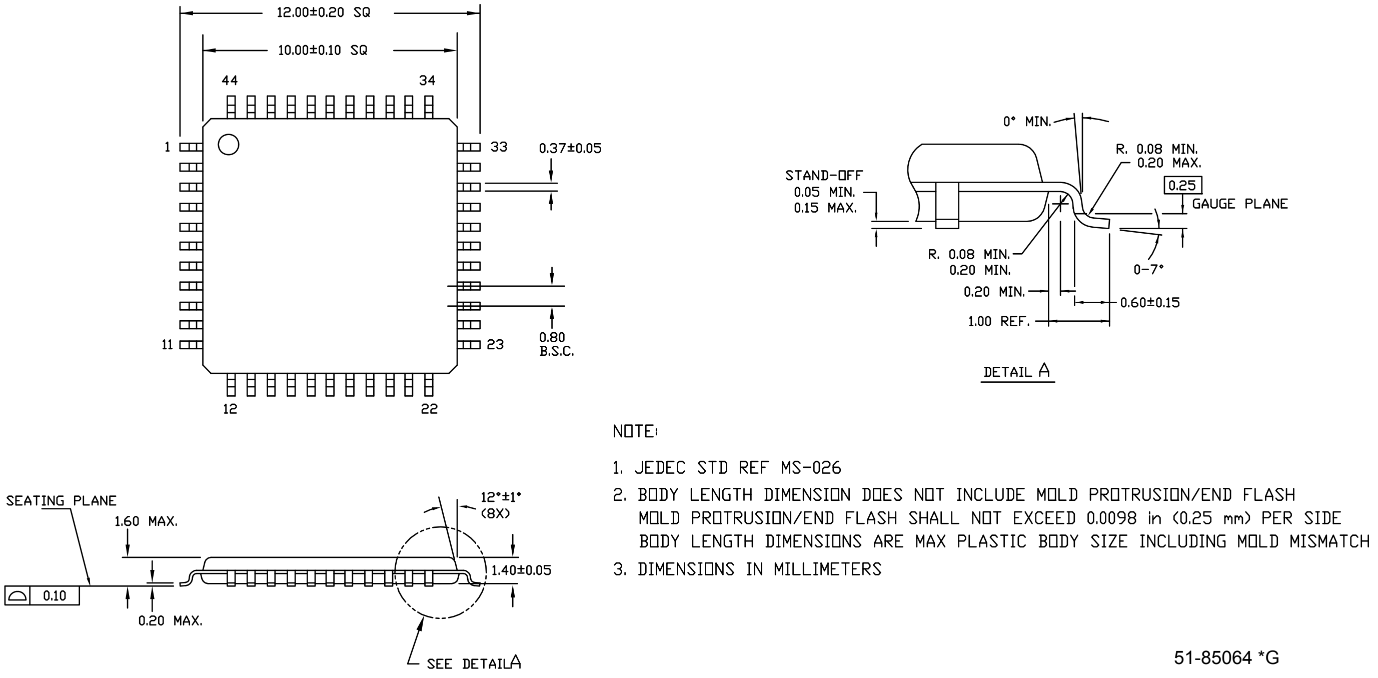
Figure 6. 48-pin TQFP Package Outline



DIMENSIONS ARE IN MILLIMETERS

51-85135 *C

Figure 7. 44-pin TQFP Package Outline

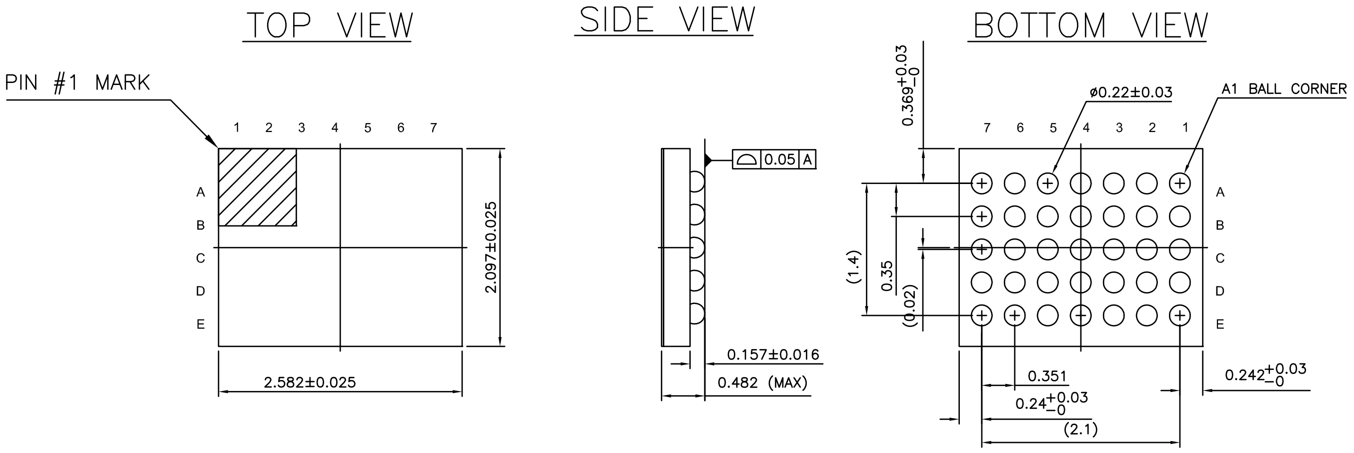


NOTE:

1. JEDEC STD REF MS-026
2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH
   MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.0098 in (0.25 mm) PER SIDE
   BODY LENGTH DIMENSIONS ARE MAX PLASTIC BODY SIZE INCLUDING MOLD MISMATCH
3. DIMENSIONS IN MILLIMETERS

51-85064 *G

Figure 10. 35-Ball WLCSP Package Outline



ALL DIMENSIONS ARE IN MM
JEDEC Publication 95; Design Guide 4.18

002-09958 *C

Acronyms

Table 42. Acronyms Used in this Document

Acronym	Description
abus	analog local bus
ADC	analog-to-digital converter
AG	analog global
AHB	AMBA (advanced microcontroller bus architecture) high-performance bus, an ARM data transfer bus
ALU	arithmetic logic unit
AMUXBUS	analog multiplexer bus
API	application programming interface
APSR	application program status register
ARM®	advanced RISC machine, a CPU architecture
ATM	automatic thump mode
BW	bandwidth
CAN	Controller Area Network, a communications protocol
CMRR	common-mode rejection ratio
CPU	central processing unit
CRC	cyclic redundancy check, an error-checking protocol
DAC	digital-to-analog converter, see also IDAC, VDAC
DFB	digital filter block
DIO	digital input/output, GPIO with only digital capabilities, no analog. See GPIO.
DMIPS	Dhrystone million instructions per second
DMA	direct memory access, see also TD
DNL	differential nonlinearity, see also INL
DNU	do not use
DR	port write data registers
DSI	digital system interconnect
DWT	data watchpoint and trace
ECC	error correcting code
ECO	external crystal oscillator
EEPROM	electrically erasable programmable read-only memory
EMI	electromagnetic interference
EMIF	external memory interface
EOC	end of conversion
EOF	end of frame
EPSR	execution program status register
ESD	electrostatic discharge
ETM	embedded trace macrocell
FIR	finite impulse response, see also IIR
FPB	flash patch and breakpoint
FS	full-speed
GPIO	general-purpose input/output, applies to a PSoC pin
HVI	high-voltage interrupt, see also LVI, LVD
IC	integrated circuit
IDAC	current DAC, see also DAC, VDAC
IDE	integrated development environment
I^2C, or IIC	Inter-Integrated Circuit, a communications protocol
IIR	infinite impulse response, see also FIR
ILO	internal low-speed oscillator, see also IMO
IMO	internal main oscillator, see also ILO
INL	integral nonlinearity, see also DNL
I/O	input/output, see also GPIO, DIO, SIO, USBIO
IPOR	initial power-on reset
IPSR	interrupt program status register
IRQ	interrupt request
ITM	instrumentation trace macrocell
LCD	liquid crystal display
LIN	Local Interconnect Network, a communications protocol.
LR	link register
LUT	lookup table
LVD	low-voltage detect, see also LVI
LVI	low-voltage interrupt, see also HVI
LVTTL	low-voltage transistor-transistor logic
MAC	multiply-accumulate
MCU	microcontroller unit
MISO	master-in slave-out
NC	no connect
NMI	nonmaskable interrupt
NRZ	non-return-to-zero
NVIC	nested vectored interrupt controller
NVL	nonvolatile latch, see also WOL
opamp	operational amplifier
PAL	programmable array logic, see also PLD

Document Conventions

Units of Measure

Table 43. Units of Measure

Symbol	Unit of Measure
°C	degrees Celsius
dB	decibel
fF	femto farad
Hz	hertz
KB	1024 bytes
kbps	kilobits per second
Khr	kilohour
kHz	kilohertz
kΩ	kilo ohm
ksps	kilosamples per second
LSB	least significant bit
Mbps	megabits per second
MHz	megahertz
MΩ	mega-ohm
Msps	megasamples per second
µA	microampere
µF	microfarad
µH	microhenry
µs	microsecond
µV	microvolt
µW	microwatt
mA	milliampere
ms	millisecond
mV	millivolt
nA	nanoampere
ns	nanosecond
nV	nanovolt
Ω	ohm
pF	picofarad
ppm	parts per million
ps	picosecond
s	second
sps	samples per second
sqrtHz	square root of hertz
V	volt

Revision History

Description Title: PSoC® 4: PSoC 4100S Family Datasheet Programmable System-on-Chip (PSoC) Document Number: 002-00122				
Revision	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
**	4883809	WKA	08/28/2015	New datasheet
*A	4992376	WKA	10/30/2015	Updated Pinouts. Added V_{DDD} ≥ 2.2V at –40 °C under Conditions for specs SID247A, SID90, SID92. Updated Table 15. Updated Ordering Information.
*B	5037826	SLAN	12/08/2015	Changed datasheet status to Preliminary
*C	5060691	WKA	12/22/2015	Updated SCBs from 2 to 3. Updated SRAM size to 8 KB. Changed WLCSP package to 35-ball WLCSP. Updated Pin List and Alternate Pin Functions. Updated Ordering Information.
*D	5139206	WKA	02/16/2016	Added Errata. Added 35 WLCSP package details. Updated theta J_A and J_C values for all packages. Updated copyright information at the end of the document.
*E	5173961	WKA	03/15/2016	Updated values for SID79, BID194. SID175, and SID176. Updated CSD and IDAC Specifications. Updated 10-bit CapSense ADC Specifications.
*F	5330930	WKA	07/27/2016	Updated CSD and IDAC Specifications. Updated 10-bit CapSense ADC Specifications. Removed errata.
*G	5473409	WKA	10/13/2016	Added 44 TQFP pin and package details.
*H	5561833	WKA	01/09/2017	Updated Figure 3. Changed PRGIO references to Smart I/O. Updated DC Specifications. Updated Ordering Information.